

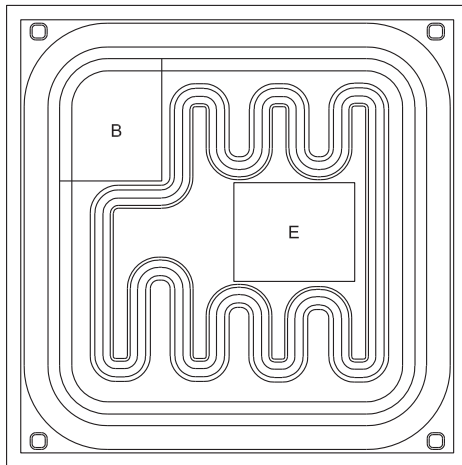
**PROCESS CP191V**  
**Small Signal Transistor**  
NPN - Amp/Switch Transistor Chip



**PROCESS DETAILS**

Process	EPITAXIAL PLANAR
Die Size	16.5 x 16.5 MILS
Die Thickness	7.1 MILS
Base Bonding Pad Area	3.5 x 4.3 MILS
Emitter Bonding Pad Area	3.5 x 4.3 MILS
Top Side Metalization	Al - 30,000Å
Back Side Metalization	Au-As - 13,000Å

**GEOMETRY**



BACKSIDE COLLECTOR R3

**GROSS DIE PER 4 INCH WAFER**  
**41,699**

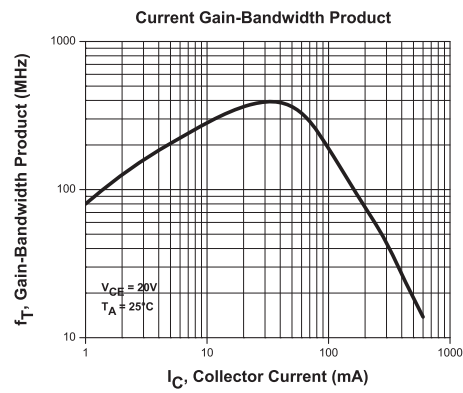
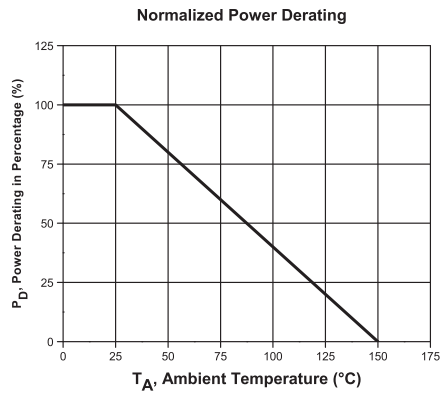
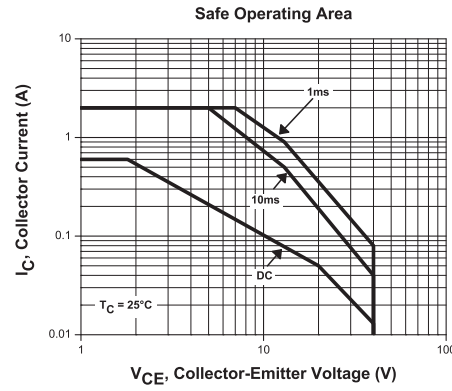
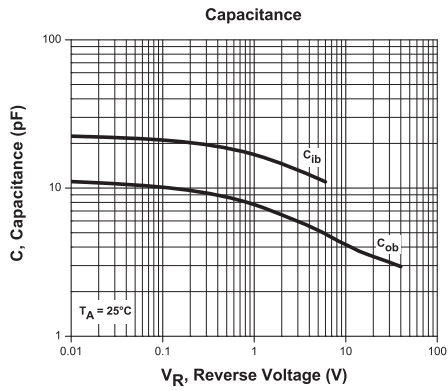
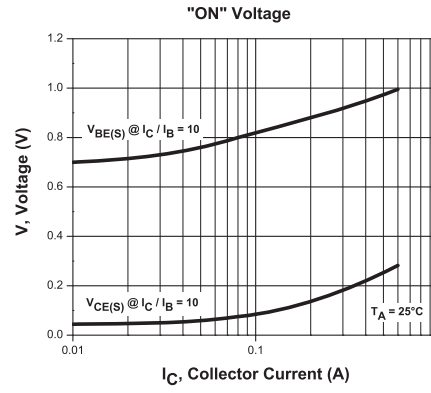
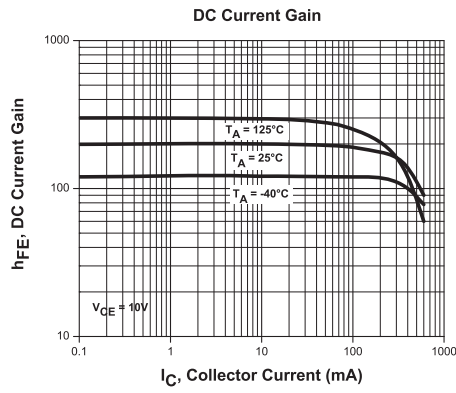
**PRINCIPAL DEVICE TYPES**

- CMLT2222A
- CMLT2207
- CMLM2205
- CMKT2207

R1 (22-March 2010)

# PROCESS CP191V

## Typical Electrical Characteristics



R1 (22-March 2010)